removing a portion of the amorphous semiconductor film to form a metal element addition region, where a metal element is capable of promoting crystallization of the amorphous semiconductor film;

selectively introducing the metal element in contact with the metal element addition region;

heating the amorphous semiconductor film so that crystals grow in parallel to the insulating surface from the metal element addition region,

wherein the metal element is selectively introduced by coating a solution containing the metal element therein and applying water repellence of the semiconductor film to the solution. --

Please add claims 8-19.

-- 8. (New) A method according to claim 1, further comprising:

irradiating the crystallized semiconductor film with a laser light.

9. (New) A method according to claim 1, further comprising:

heating the crystallized semiconductor film in an atmosphere comprising a halogen element.

10. (New) A method according to claim 4, further comprising:

irradiating the crystallized semiconductor film with a laser light.

11. (New) A method according to claim 4, further comprising:

heating the crystallized semiconductor film in an atmosphere comprising a halogen element.

B2 cont

12. (New) A method according to claim 6, further comprising:

irradiating the crystallized semiconductor film with a laser light.

13. (New) A method according to claim 6, further comprising:

heating the crystallized semiconductor film in an atmosphere comprising a halogen element.

14. (New) A method of manufacturing an EL display device, said method comprising the steps of:

forming an amorphous semiconductor film comprising Si_xGe_{1-x} ($0<x<1$) on an insulating surface;

selectively introducing a metal element into a first portion of the amorphous semiconductor film while the metal element is not introduced into a second portion of the amorphous semiconductor film, said metal element being capable of promoting crystallization of the amorphous semiconductor film;

heating the amorphous semiconductor film to form a crystalline semiconductor film;

B2 cont

wherein a crystal growth vertically proceeds in the first portion while the crystal growth laterally proceeds from the first portion in the second portion;

patterning the crystalline semiconductor film to form a first crystalline semiconductor island and a second crystalline semiconductor island using the first and second portions, respectively;

forming a first gate electrode and a second gate electrode adjacent to the first and second crystalline semiconductor islands with a gate insulating film, respectively;

introducing a first inpurity into the first crystalline semiconductor island to form a first source region, a first drain region and a first channel region of a first thin film transistor;

introducing a second impurity into the second crystalline semiconductor island to form a second source region,

a second drain region and a second channel region of a second thin film transistor,

wherein the metal element is selectively introduced into the first portion of the amorphous semiconductor film by coating a solution containing the metal element therein and applying water repellency of the semiconductor film to the solution.

15. (New) A method according to claim 14,

wherein the metal element is at least one selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu and Au.

16. (New) A method according to claim 14, further comprising:

irradiating the crystalline semiconductor film with a laser light.

17. (New) A method according to claim 14, further comprising:

heating the crystalline semiconductor film in an atmosphere comprising a halogen element.

18. (New) A method according to claim 14,